Abstracts

Transit Time Effect in High-Frequency Characteristics of HBTs

---

S. Lee and A. Gopinath. "Transit Time Effect in High-Frequency Characteristics of HBTs." 1992 MTT-S International Microwave Symposium Digest 92.1 (1992 Vol. I [MWSYM]): 271-272.

We present simulation results that show negative output resistance may exist at frequencies beyond f/sub max/ in the conventional mesa emitter-up AlGaAs/GaAs heterojunction bipolar transistors. It is shown that larger collector transit time is preferable choice to increasing base transit time in the design of this structure.

❑ Return to main document.

Click on title for a complete paper.